

BS Elektronik Service GmbH

AlGaInP/Si Red Orange Chip ---540UOH

1. Scope

- AlGaInP High- Brightness LED chip.

2. Structure

- AlGaInP on Silicon
- N Electrode (cathode) side : Gold.
- P Electrode (anode) side : Gold alloy.

3. Size

- Chip size : 40 mil × 40 mil (1mm × 1 mm)
- Pattern drawing : per fig. 1

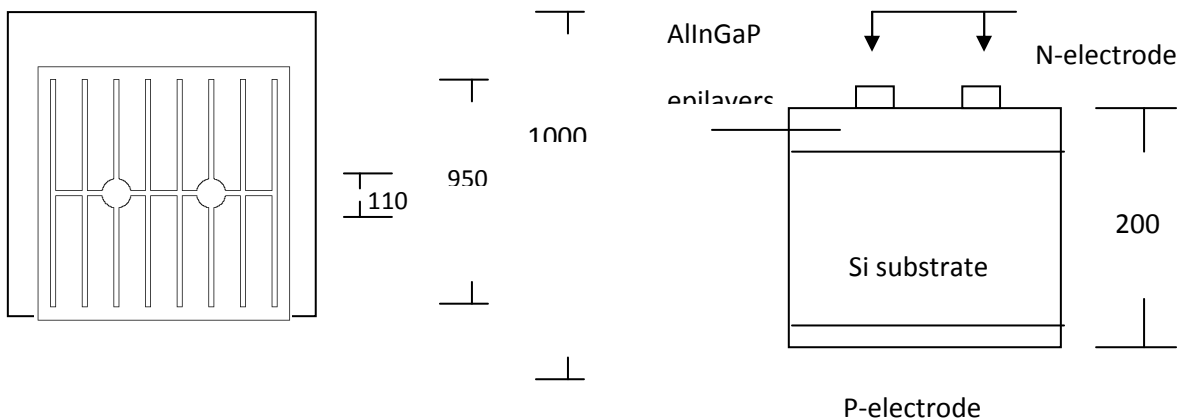
4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 350 \text{ mA}$		2.5		V
Reverse Voltage	I_R	$I_R = 10 \text{ V}$			10	μA
Luminous Intensity	I_v	$I_F = 350 \text{ mA}$	※			mcd
Wavelength	λ_d	$I_F = 20 \text{ mA}$	620	625	630	nm
Spectrum Width of Half Value	$\Delta \lambda$	$I_F = 20 \text{ mA}$		20		nm

* R: ≥ 4300 , S: ≥ 5000 , T: ≥ 5700 , U: ≥ 6500

Maximum reverse-biased voltage < 60V; therefore, V_z test is forbidden.



Recommendation for bonding condition:

— bonding force 40 g, bonding temperature 280C, bonding time 20 ms.